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## CD++ Model Data Form

Title: Three - Dimentional Si Etching

Type: Cell-DEVS Model

Acronym/Short name: 3D\_Etching

Purpose for which Developed: Simulation of a 3 dimensional Si etching process

Other Applications for which it is Suitable: It can be used for 2 dimensional

Date Developed/Implemented: 16/11/2012

Domain: Complex physical systems

Current Version: 1.0

URL:

Description (including characteristics): In our simulation, we apply cell-DEVS into simulating Si wet etching process. Wet etching is the process of using chemical reaction between some special liquid and wafer to remove the part uncovered by the photoresist. As wet etching is a pure chemical process, it has advanced selectivity which stops at current thin-film without affecting other material. Cell-DEVS is a formalism used to simulate the complex physical model into cell space model, which is required to be time discrete, space discrete and state discrete. Considering from the Si stereochemical structure, each Si atom can be seen as a cell and they are distributed discretely in Si molecule.

Links to Related Documents

Short Title:

URL:

Description:

Keywords: 3D, Cell-DEVS, Si etching, wet etching

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Comments: